

TLP2466

1. Applications

- Factory Networking
- High-Speed Digital Interfacing for Instrumentation and Control Devices
- Plasma Display Panels (PDPs)

2. General

The Toshiba TLP2466 consists of a high-output GaAs light-emitting diode coupled with a high-speed photo-diode-transistor chip. The TLP2466 guarantees operation at up to 125°C and on supplies both 3.3 V and 5 V. It is offered in the SO8 package. The TLP2466 has a totem-pole output that can both sink and source current. An internal noise shield provides a guaranteed common-mode transient immunity of ± 20 kV/ μ s.

3. Features

- (1) Inverter logic type (Totem pole output)
- (2) Package: SO8
- (3) Operating temperature: -40 to 125°C
- (4) Supply voltage: 2.7 to 5.5 V
- (5) Data transfer rate: 20 MBd (typ.) (NRZ)
- (6) Threshold input current: 3.5 mA (max)
- (7) Supply current: 3 mA (max)
- (8) Common-mode transient immunity: ± 20 kV/ μ s (min)
- (9) Isolation voltage: 3750 Vrms (min)
- (10) Safety standards

UL-approved: UL1577, File No.E67349

cUL-approved: CSA Component Acceptance Service No.5A File No.E67349

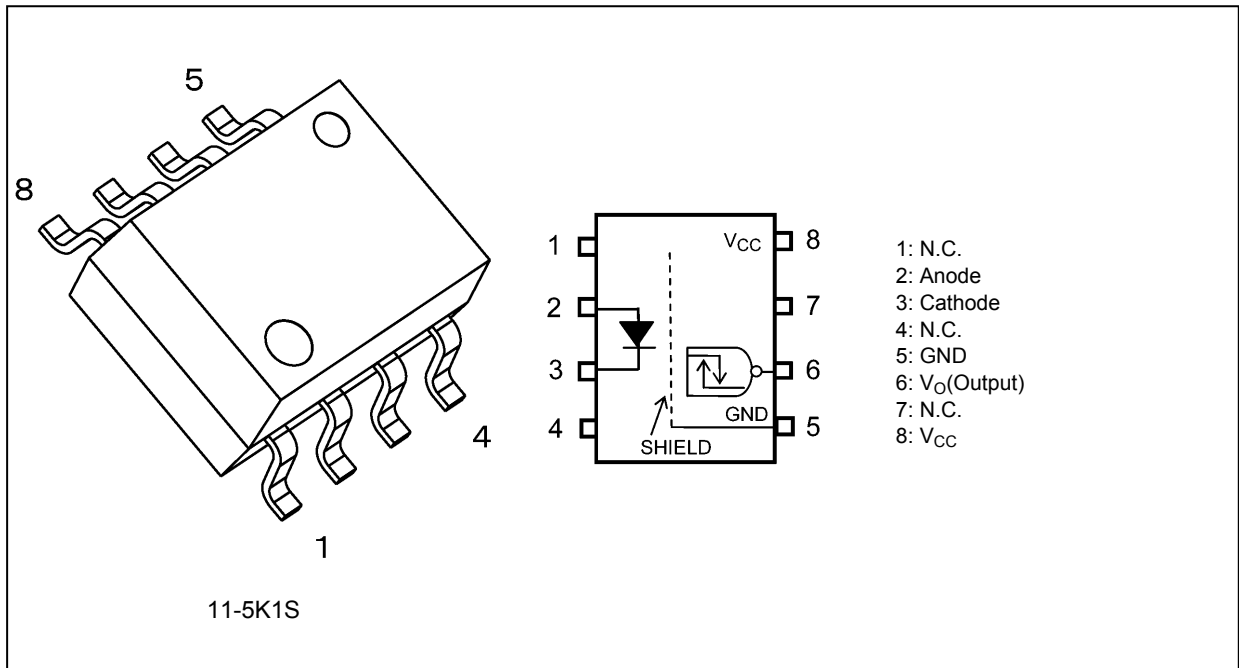
VDE-approved: EN60747-5-5 (**Note 1**)

Note 1: When an EN60747-5-5 approved type is needed, please designate the **Option (V4)**.

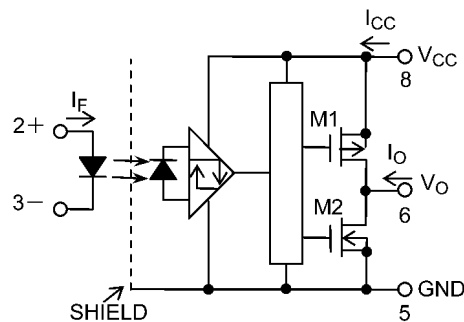
Start of commercial production

2011-04

4. Packaging and Pin Configuration



5. Internal Circuit (Note)



Note: A 0.1 μ F bypass capacitor must be connected between pin 8 and pin 5.

6. Principle of Operation

6.1. Truth Table

Input	LED	M1	M2	Output
H	ON	OFF	ON	L
L	OFF	ON	OFF	H

6.2. Mechanical Parameters

Characteristics	Min	Unit
Creepage distances	4.2	mm
Clearance distances	4.2	
Internal isolation thickness	—	

7. Absolute Maximum Ratings (Note) (Unless otherwise specified, T_a = 25°C)

	Characteristics	Symbol	Note	Rating	Unit
LED	Input forward current	I _F		25	mA
	Input forward current derating (T _a ≥ 110°C)	ΔI _F /ΔT _a		-0.67	mA/°C
	Input forward current (pulsed)	I _{FP}	(Note 1)	40	mA
	Input forward current derating (pulsed) (T _a ≥ 110°C)	ΔI _{FP} /ΔT _a		-1.0	mA/°C
	Input power dissipation	P _D		40	mW
	Input power dissipation derating (T _a ≥ 110°C)	ΔP _D /ΔT _a		-1.0	mW/°C
	Input reverse voltage	V _R		5	V
Detector	Output current	I _O		10	mA
	Output voltage	V _O		6	V
	Supply voltage	V _{CC}		6	
	Output power dissipation	P _O		60	mW
	Output power dissipation derating (T _a ≥ 110°C)	ΔP _O /ΔT _a		-1.5	mW/°C
Common	Operating temperature	T _{opr}		-40 to 125	°C
	Storage temperature	T _{stg}		-55 to 150	
	Lead soldering temperature (10 s)	T _{sol}		260	
	Isolation voltage AC, 60 s, R.H. ≤ 60%	BV _S	(Note 2)	3750	Vrms

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Pulse width (PW) ≤ 1 ms, duty = 50 %

Note 2: This device is considered as a two-terminal device: Pins 1, 2, 3 and 4 are shorted together, and pins 5, 6, 7 and 8 are shorted together.

8. Recommended Operating Conditions (Note)

Characteristics	Symbol	Note	Min	Typ.	Max	Unit
Input on-state current	I _{F(ON)}	(Note 1)	4.5	—	15	mA
Input off-state voltage	V _{F(OFF)}		0	—	0.8	V
Supply voltage	V _{CC}	(Note 2)	2.7	3.3/5.0	5.5	
Operating temperature	T _{opr}	(Note 2)	-40	—	125	°C

Note: The recommended operating conditions are given as a design guide necessary to obtain the intended performance of the device. Each parameter is an independent value. When creating a system design using this device, the electrical characteristics specified in this datasheet should also be considered.

Note: A ceramic capacitor (0.1 μF) should be connected between pin 8 and pin 5 to stabilize the operation of a high-gain linear amplifier. Otherwise, this photocoupler may not switch properly. The bypass capacitor should be placed within 1 cm of each pin.

Note 1: The rise and fall times of the input on-current should be less than 0.5 μs.

Note 2: Denotes the operating range, not the recommended operating condition.

9. Electrical Characteristics (Note)
 (Unless otherwise specified, $T_a = -40$ to 125°C , $V_{CC} = 2.7$ to 5.5 V)

Characteristics	Symbol	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Input forward voltage	V_F	—	$I_F = 10$ mA, $T_a = 25^\circ\text{C}$	1.45	1.55	1.7	V
Input forward voltage temperature coefficient	$\Delta V_F / \Delta T_a$	—	$I_F = 10$ mA	—	-2.0	—	mV/ $^\circ\text{C}$
Input reverse current	I_R	—	$V_R = 5$ V, $T_a = 25^\circ\text{C}$	—	—	10	μA
Input capacitance	C_t	—	$V = 0$ V, $f = 1$ MHz, $T_a = 25^\circ\text{C}$	—	60	—	pF
Low-level output voltage	V_{OL}	Fig. 12.1.1	$I_F = 14$ mA, $I_O = 4$ mA	—	—	0.4	V
High-level output voltage	V_{OH}	Fig. 12.1.2	$V_F = 1.05$ V, $I_O = -4$ mA, $V_{CC} = 3.3$ V	2.3	—	—	V
			$V_F = 1.05$ V, $I_O = -4$ mA, $V_{CC} = 5$ V	4	—	—	
Low-level supply current	I_{CCL}	Fig. 12.1.3	$I_F = 14$ mA	—	—	3	mA
High-level supply current	I_{CCH}	Fig. 12.1.4	$I_F = 0$ mA	—	—	3	
Threshold input current (H/L)	I_{FHL}	—	$I_O = 1.6$ mA, $V_O < 0.4$ V	—	—	3.5	

Note: All typical values are at $T_a = 25^\circ\text{C}$.

10. Isolation Characteristics (Unless otherwise specified, $T_a = 25^\circ\text{C}$)

Characteristics	Symbol	Note	Test Conditions	Min	Typ.	Max	Unit
Total capacitance (input to output)	C_S	(Note 1)	$V_S = 0$ V, $f = 1$ MHz	—	0.8	—	pF
Isolation resistance	R_S	(Note 1)	$V_S = 500$ V, R.H. $\leq 60\%$	1×10^{12}	10^{14}	—	Ω
Isolation voltage	BV_S		AC, 60 s	3750	—	—	Vrms
			AC, 1 s in oil	—	10000	—	
			DC, 60 s in oil	—	10000	—	Vdc

Note 1: This device is considered as a two-terminal device: Pins 1, 2, 3 and 4 are shorted together, and pins 5, 6, 7 and 8 are shorted together.

11. Switching Characteristics (Note)

11.1. Switching Characteristics (1)
 (Unless otherwise specified, $T_a = -40$ to 125°C , $V_{CC} = 2.7$ to 3.6 V)

Characteristics	Symbol	Note	Test Circuit	Test Condition	Min	Typ.	Max	Unit	
Propagation delay time (H/L)	t_{pHL}	(Note 1)	Fig. 12.1.5	$I_F = 0 \rightarrow 14$ mA, $R_{IN} = 100 \Omega$, $C_L = 15$ pF	—	30	40	ns	
Propagation delay time (L/H)	t_{pLH}	(Note 1)			$I_F = 14 \rightarrow 0$ mA, $R_{IN} = 100 \Omega$, $C_L = 15$ pF	—	25		40
Pulse width distortion	$ t_{pHL} - t_{pLH} $	(Note 1)			$I_F = 14$ mA, $R_{IN} = 100 \Omega$, $C_L = 15$ pF	—	5		25
Propagation delay skew (device to device)	t_{psk}	(Note 1), (Note 2)				-30	—		30
Propagation delay time (H/L)	t_{pHL}	(Note 1)	Fig. 12.1.5	$I_F = 0 \rightarrow 6$ mA, $R_{IN} = 100 \Omega$, $C_L = 15$ pF	—	36	55		
Propagation delay time (L/H)	t_{pLH}	(Note 1)			$I_F = 6 \rightarrow 0$ mA, $R_{IN} = 100 \Omega$, $C_L = 15$ pF	—	26		55
Pulse width distortion	$ t_{pHL} - t_{pLH} $	(Note 1)			$I_F = 6$ mA, $R_{IN} = 100 \Omega$, $C_L = 15$ pF	—	10		30
Propagation delay skew (device to device)	t_{psk}	(Note 1), (Note 2)				-30	—		30
Fall time	t_f	(Note 1)	Fig. 12.1.5	$I_F = 0 \rightarrow 14$ mA, $R_{IN} = 100 \Omega$, $C_L = 15$ pF	—	15	—		
Rise time	t_r	(Note 1)			$I_F = 14 \rightarrow 0$ mA, $R_{IN} = 100 \Omega$, $C_L = 15$ pF	—	15		—
Common-mode transient immunity at output high	CM_H		Fig. 12.1.6	$V_{CM} = 1000$ V _{p-p} , $I_F = 0$ mA, $V_{O(min)} = 2$ V, $V_{CC} = 3.3$ V, $T_a = 25^\circ\text{C}$	± 20	± 25	—	kV/ μ s	
Common-mode transient immunity at output low	CM_L				$V_{CM} = 1000$ V _{p-p} , $I_F = 14$ mA, $V_{O(max)} = 0.4$ V, $V_{CC} = 3.3$ V, $T_a = 25^\circ\text{C}$	± 20	± 25		—

Note: All typical values are at $T_a = 25^\circ\text{C}$.

Note 1: $f = 5$ MHz, duty = 50 %, input current $t_r = t_f = 5$ ns, C_L is approximately 15 pF which includes probe and stray wiring capacitance.

Note 2: The propagation delay skew, t_{psk} , is equal to the magnitude of the worst-case difference in t_{pHL} and/or t_{pLH} that will be seen between units at the same given conditions (supply voltage, input current, temperature, etc).

11.2. Switching Characteristics (2)
 (Unless otherwise specified, $T_a = -40$ to 125°C , $V_{CC} = 4.5$ to 5.5 V)

Characteristics	Symbol	Note	Test Circuit	Test Condition	Min	Typ.	Max	Unit	
Propagation delay time (H/L)	t_{pHL}	(Note 1)	Fig. 12.1.5	$I_F = 0 \rightarrow 14$ mA, $R_{IN} = 100 \Omega$, $C_L = 15$ pF	—	33	45	ns	
Propagation delay time (L/H)	t_{pLH}	(Note 1)			$I_F = 14 \rightarrow 0$ mA, $R_{IN} = 100 \Omega$, $C_L = 15$ pF	—	25		45
Pulse width distortion	$ t_{pHL} - t_{pLH} $	(Note 1)			$I_F = 14$ mA, $R_{IN} = 100 \Omega$, $C_L = 15$ pF	—	8		25
Propagation delay skew (device to device)	t_{psk}	(Note 1), (Note 2)				-30	—		30
Propagation delay time (H/L)	t_{pHL}	(Note 1)	Fig. 12.1.5	$I_F = 0 \rightarrow 6$ mA, $R_{IN} = 100 \Omega$, $C_L = 15$ pF	—	40	55		
Propagation delay time (L/H)	t_{pLH}	(Note 1)			$I_F = 6 \rightarrow 0$ mA, $R_{IN} = 100 \Omega$, $C_L = 15$ pF	—	28		55
Pulse width distortion	$ t_{pHL} - t_{pLH} $	(Note 1)			$I_F = 6$ mA, $R_{IN} = 100 \Omega$, $C_L = 15$ pF	—	12		30
Propagation delay skew (device to device)	t_{psk}	(Note 1), (Note 2)				-30	—		30
Fall time	t_f	(Note 1)	Fig. 12.1.5	$I_F = 0 \rightarrow 14$ mA, $R_{IN} = 100 \Omega$, $C_L = 15$ pF	—	15	—		
Rise time	t_r	(Note 1)			$I_F = 14 \rightarrow 0$ mA, $R_{IN} = 100 \Omega$, $C_L = 15$ pF	—	15		—
Common-mode transient immunity at output high	CM_H		Fig. 12.1.6	$V_{CM} = 1000$ V _{p-p} , $I_F = 0$ mA, $V_{O(min)} = 4$ V, $V_{CC} = 5$ V, $T_a = 25^\circ\text{C}$	± 20	± 25	—	kV/ μs	
Common-mode transient immunity at output low	CM_L				$V_{CM} = 1000$ V _{p-p} , $I_F = 14$ mA, $V_{O(max)} = 0.4$ V, $V_{CC} = 5$ V, $T_a = 25^\circ\text{C}$	± 20	± 25		—

Note: All typical values are at $T_a = 25^\circ\text{C}$.

Note 1: $f = 5$ MHz, duty = 50 %, input current $t_r = t_f = 5$ ns, C_L is approximately 15 pF which includes probe and stray wiring capacitance.

Note 2: The propagation delay skew, t_{psk} , is equal to the magnitude of the worst-case difference in t_{pHL} and/or t_{pLH} that will be seen between units at the same given conditions (supply voltage, input current, temperature, etc).

12. Test Circuits and Characteristics Curves

12.1. Test Circuits

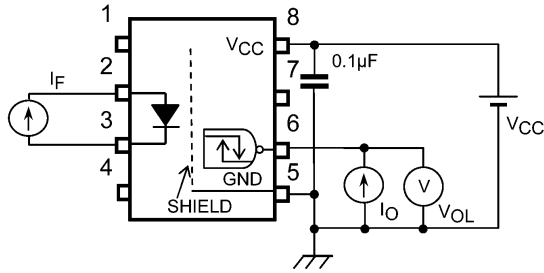


Fig. 12.1.1 VOL Test Circuit

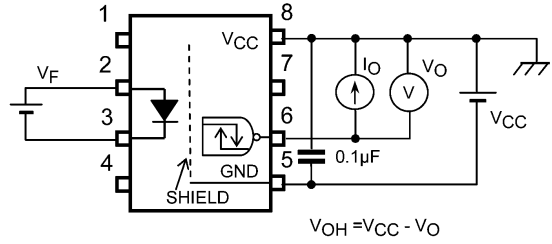


Fig. 12.1.2 VOH Test Circuit

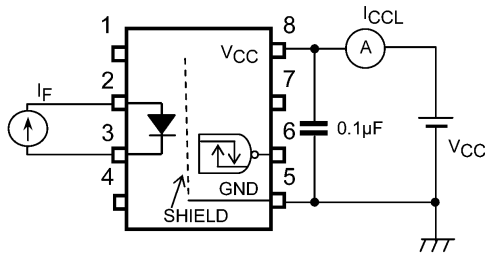


Fig. 12.1.3 ICCL Test Circuit

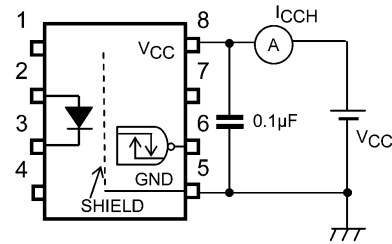
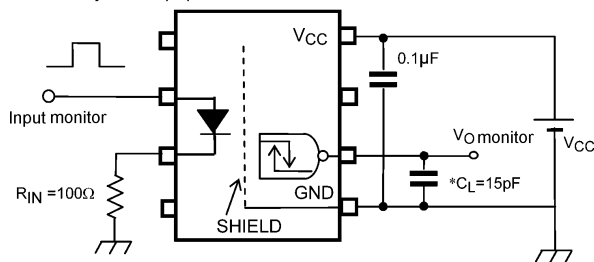


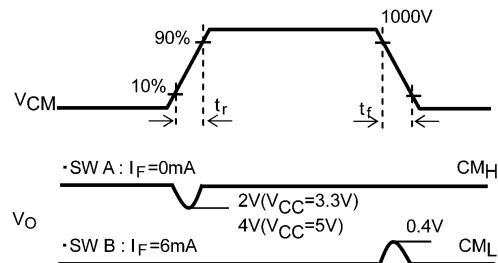
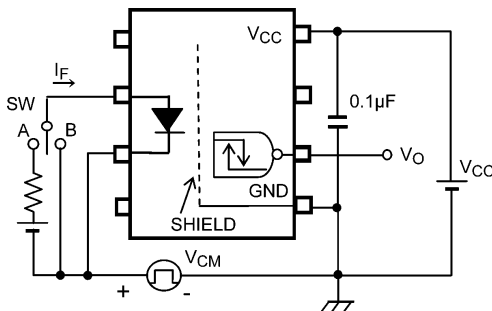
Fig. 12.1.4 ICCH Test Circuit

$I_F = 6/14\text{mA (P.G.)}$
 $(f = 5\text{MHz, duty} = 50\%, t_r = t_f = 5\text{ns or less})$



* C_L is approximately 15 pF which includes probe and stray wiring capacitance.
 P.G.: Pulse Generator

Fig. 12.1.5 Switching Time Test Circuit and Waveform



$$CM_L = \frac{800(V)}{t_r(\mu s)} \quad CM_H = -\frac{800(V)}{t_f(\mu s)}$$

Fig. 12.1.6 Common-Mode Transient Immunity Test Circuit and Waveform

13. Soldering and Storage

13.1. Precautions for Soldering

The soldering temperature should be controlled as closely as possible to the conditions shown below, irrespective of whether a soldering iron or a reflow soldering method is used.

- When using soldering reflow.

The soldering temperature profile is based on the package surface temperature.

(See the figure shown below, which is based on the package surface temperature.)

Reflow soldering must be performed once or twice.

The mounting should be completed with the interval from the first to the last mountings being 2 weeks.

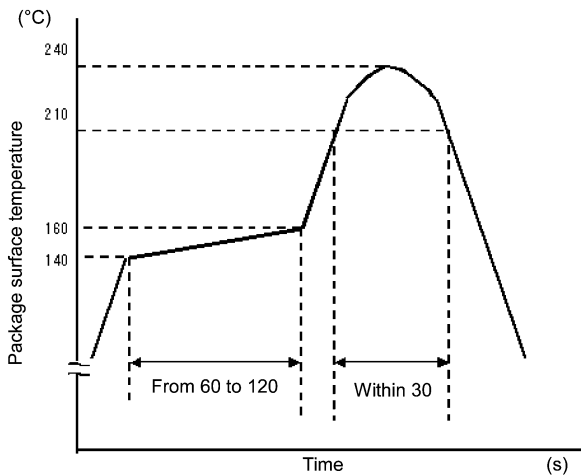


Fig. 13.1.1 An example of a temperature profile when Sn-Pb eutectic solder is used

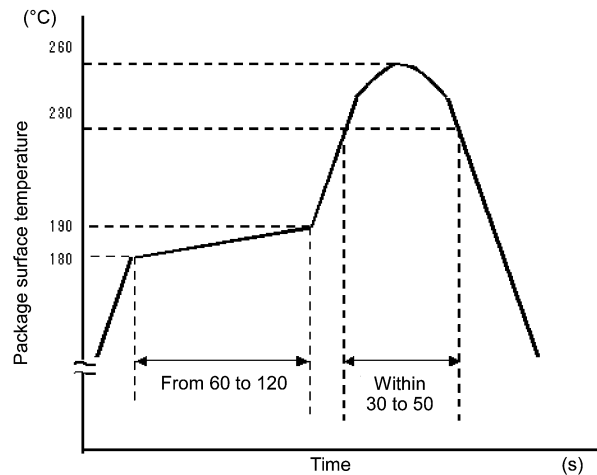


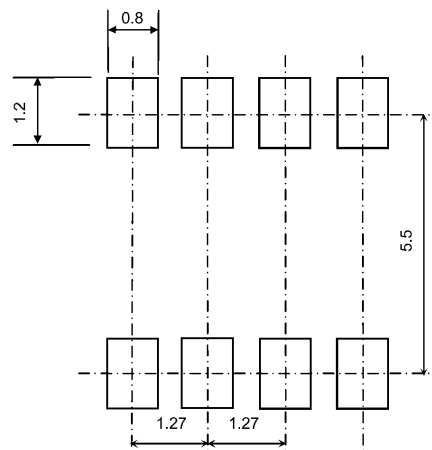
Fig. 13.1.2 An example of a temperature profile when lead(Pb)-free solder is used

- When using soldering flow (Applicable to both eutectic solder and Lead(Pb)-Free solder)
Preheat the device at a temperature of 150 °C (package surface temperature) for 60 to 120 seconds.
Mounting condition of 260 °C within 10 seconds is recommended.
Flow soldering must be performed once.
- When using soldering Iron
Complete soldering within 10 seconds for lead temperature not exceeding 260 °C or within 3 seconds not exceeding 350 °C
Heating by soldering iron must be done only once per lead.

13.2. Precautions for General Storage

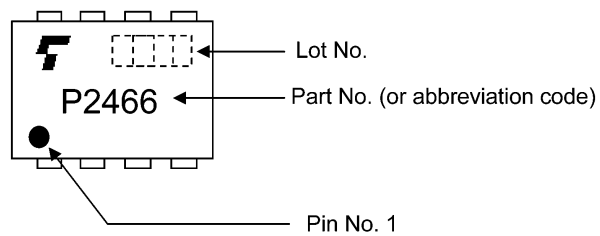
- Avoid storage locations where devices may be exposed to moisture or direct sunlight.
- Follow the precautions printed on the packing label of the device for transportation and storage.
- Keep the storage location temperature and humidity within a range of 5°C to 35°C and 45% to 75%, respectively.
- Do not store the products in locations with poisonous gases (especially corrosive gases) or in dusty conditions.
- Store the products in locations with minimal temperature fluctuations. Rapid temperature changes during storage can cause condensation, resulting in lead oxidation or corrosion, which will deteriorate the solderability of the leads.
- When restoring devices after removal from their packing, use anti-static containers.
- Do not allow loads to be applied directly to devices while they are in storage.
- If devices have been stored for more than two years under normal storage conditions, it is recommended that you check the leads for ease of soldering prior to use.

14. Land Pattern Dimensions for Reference Only



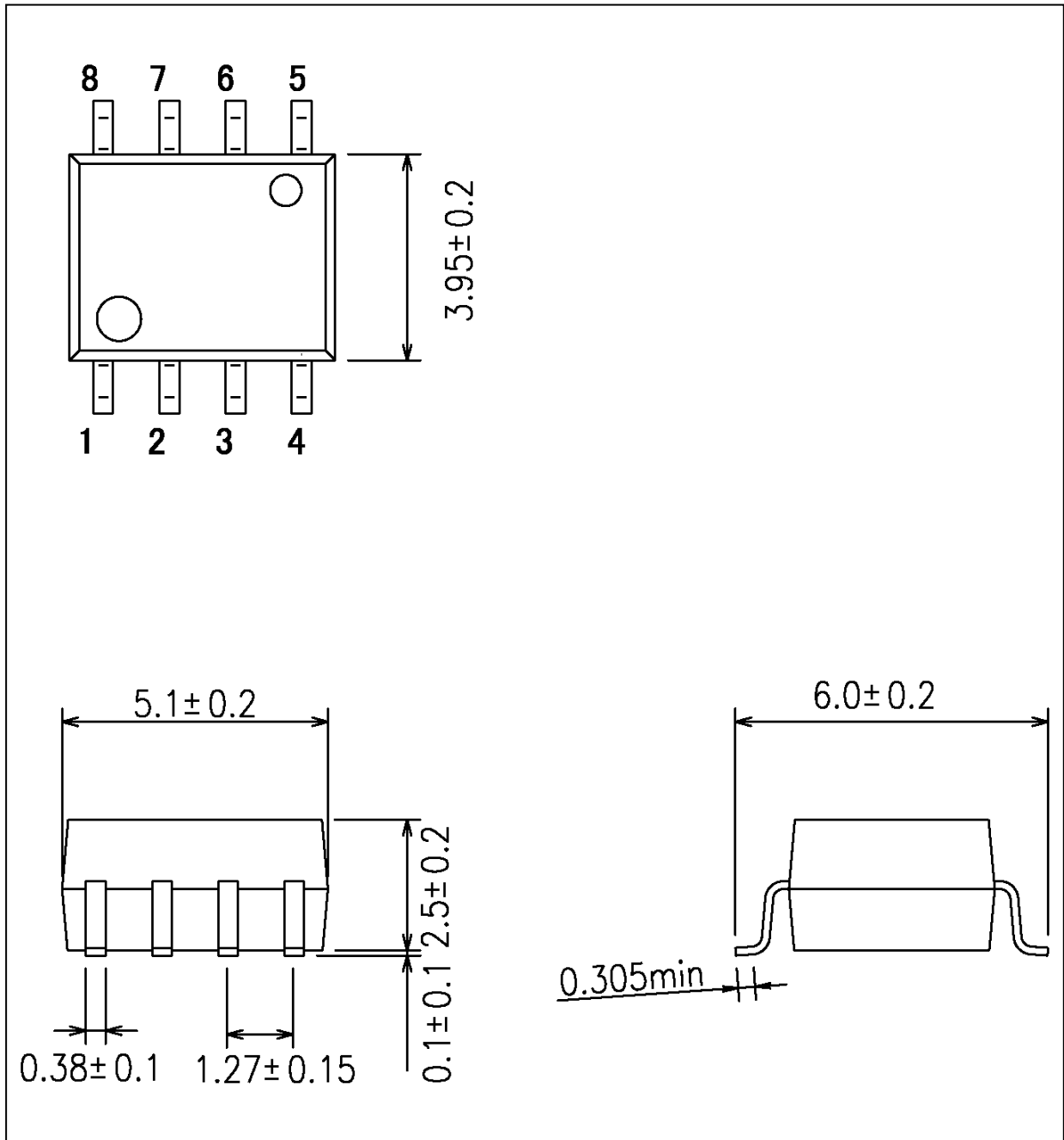
Unit: mm

15. Marking



Package Dimensions

Unit: mm



Weight: 0.11 g (typ.)

Package Name(s)
TOSHIBA: 11-5K1S

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